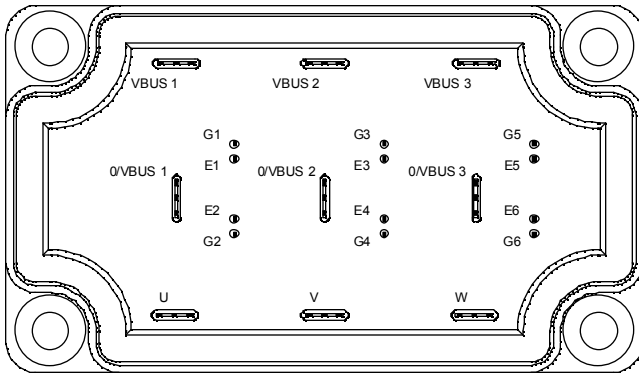
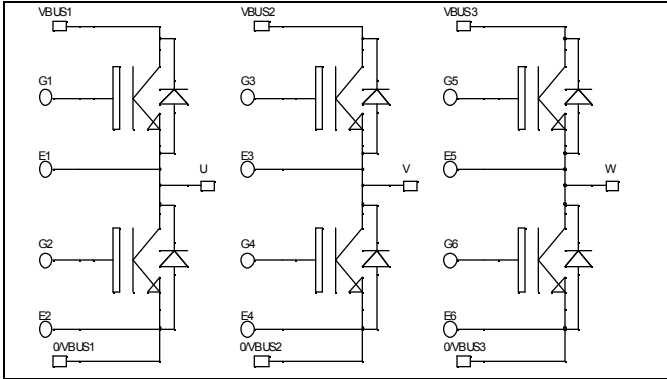


**Triple phase leg
Trench + Field Stop IGBT®
Power Module**



**$V_{CES} = 600V$
 $I_C = 75A @ T_c = 80^\circ C$**

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Trench + Field Stop IGBT® Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - Avalanche energy rated
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
 - Symmetrical design
 - Lead frames for power connections
- High level of integration

Benefits

- Stable temperature behavior
- Very rugged
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Very low (12mm) profile
- Each leg can be easily paralleled to achieve a phase leg of three times the current capability
- Module can be configured as a three phase bridge
- Module can be configured as a boost followed by a full bridge
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage	600	V
I_C	Continuous Collector Current	$T_C = 25^\circ C$	100
		$T_C = 80^\circ C$	75
I_{CM}	Pulsed Collector Current	$T_C = 25^\circ C$	140
V_{GE}	Gate - Emitter Voltage	± 20	V
P_D	Maximum Power Dissipation	$T_C = 25^\circ C$	250
RBSOA	Reverse Bias Safe Operating Area	$T_J = 150^\circ C$	150A @ 550V

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0\text{V}, V_{CE} = 600\text{V}$			250	μA
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	$V_{GE} = 15\text{V}$ $I_C = 75\text{A}$	$T_j = 25^\circ\text{C}$	1.5	1.9	V
			$T_j = 150^\circ\text{C}$	1.7		
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 600\mu\text{A}$	5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20\text{V}, V_{CE} = 0\text{V}$			600	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	$V_{GE} = 0\text{V}$		4620		pF
C_{oes}	Output Capacitance	$V_{CE} = 25\text{V}$		300		
C_{res}	Reverse Transfer Capacitance	$f = 1\text{MHz}$		140		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C)		110		ns
T_r	Rise Time	$V_{GE} = \pm 15\text{V}$		45		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 300\text{V}$		200		
T_f	Fall Time	$I_C = 75\text{A}$ $R_G = 4.7\Omega$		40		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (150°C)		120		ns
T_r	Rise Time	$V_{GE} = \pm 15\text{V}$		50		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 300\text{V}$		250		
T_f	Fall Time	$I_C = 75\text{A}$ $R_G = 4.7\Omega$		60		
E_{on}	Turn-on Switching Energy	$V_{GE} = \pm 15\text{V}$ $V_{Bus} = 300\text{V}$	$T_j = 25^\circ\text{C}$	0.35		mJ
		$I_C = 75\text{A}$	$T_j = 150^\circ\text{C}$	0.6		
E_{off}	Turn-off Switching Energy	$R_G = 4.7\Omega$	$T_j = 25^\circ\text{C}$	2.2		mJ
			$T_j = 150^\circ\text{C}$	2.6		

Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage		600			V
I_{RM}	Maximum Reverse Leakage Current	$V_R = 600\text{V}$	$T_j = 25^\circ\text{C}$		250	μA
			$T_j = 150^\circ\text{C}$		500	
I_F	DC Forward current		$T_c = 80^\circ\text{C}$	75		A
V_F	Diode Forward Voltage	$I_F = 75\text{A}$ $V_{GE} = 0\text{V}$	$T_j = 25^\circ\text{C}$	1.6	2	V
			$T_j = 150^\circ\text{C}$	1.5		
t_{rr}	Reverse Recovery Time	$I_F = 75\text{A}$ $V_R = 300\text{V}$ $di/dt = 2000\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$	100		ns
			$T_j = 150^\circ\text{C}$	150		
Q_{rr}	Reverse Recovery Charge		$T_j = 25^\circ\text{C}$	3.6		μC
			$T_j = 150^\circ\text{C}$	7.6		
E_r	Reverse Recovery Energy		$T_j = 25^\circ\text{C}$	0.85		mJ
			$T_j = 150^\circ\text{C}$	1.8		

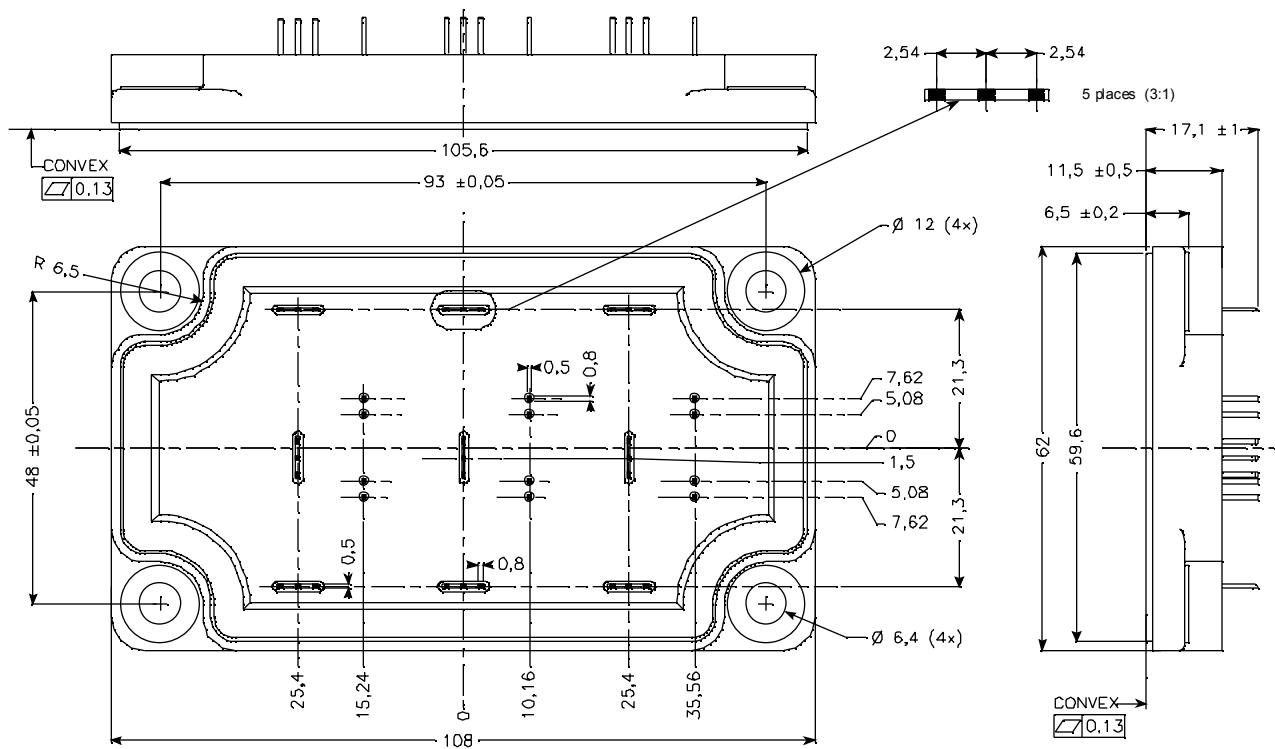
Thermal and package characteristics

Symbol Characteristic

Min Typ Max Unit

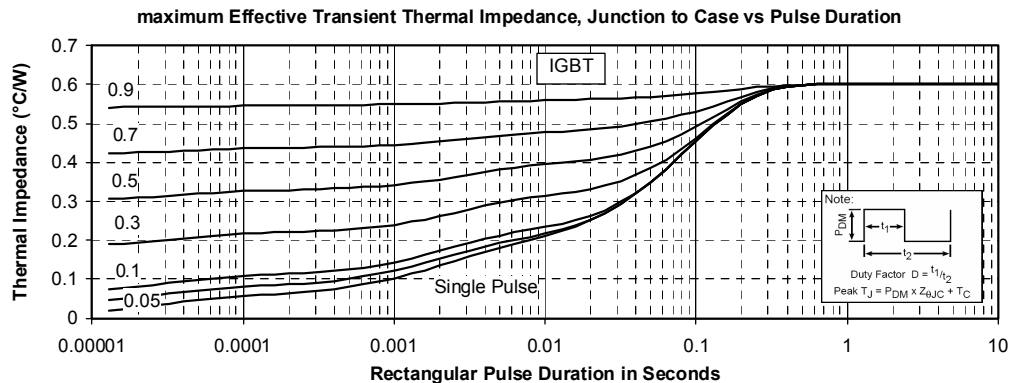
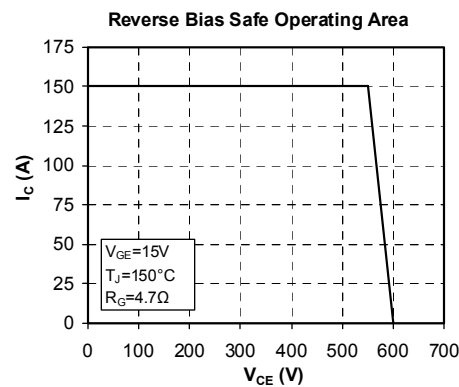
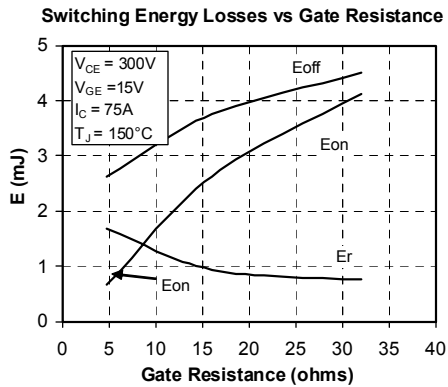
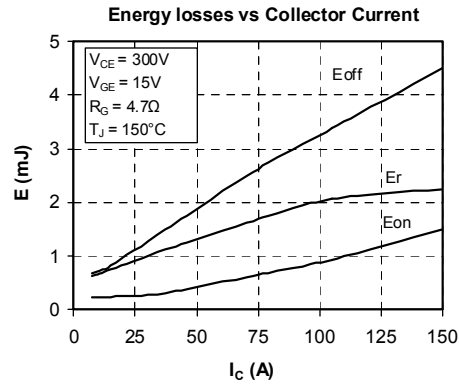
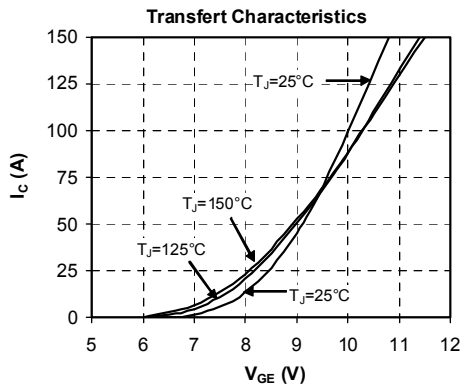
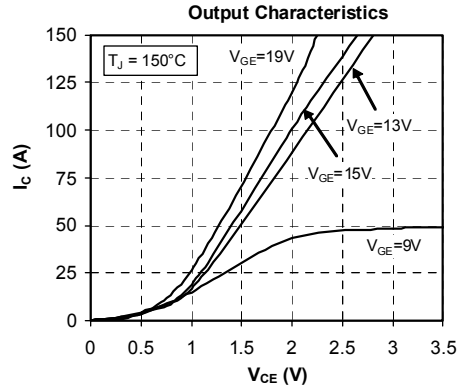
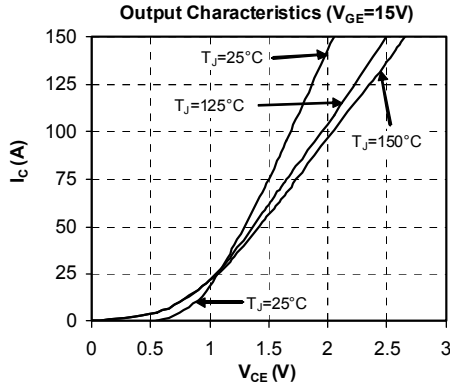
<i>R_{thJC}</i>	<i>Junction to Case Thermal Resistance</i>			<i>Unit</i>		
		<i>IGBT</i>	<i>Diode</i>			
<i>V_{ISOL}</i>	<i>RMS Isolation Voltage, any terminal to case t=1 min, I_{isol}<1mA, 50/60Hz</i>	2500		<i>V</i>		
<i>T_J</i>	<i>Operating junction temperature range</i>	-40	175	<i>°C</i>		
<i>T_{STG}</i>	<i>Storage Temperature Range</i>	-40	125			
<i>T_C</i>	<i>Operating Case Temperature</i>	-40	100			
<i>Torque</i>	<i>Mounting torque</i>	<i>To heatsink</i>	<i>M6</i>	3	5	<i>N.m</i>
<i>Wt</i>	<i>Package Weight</i>				250	<i>g</i>

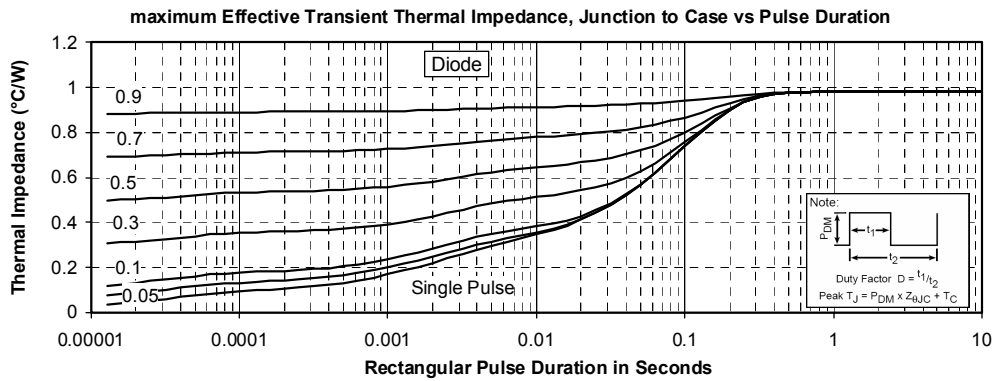
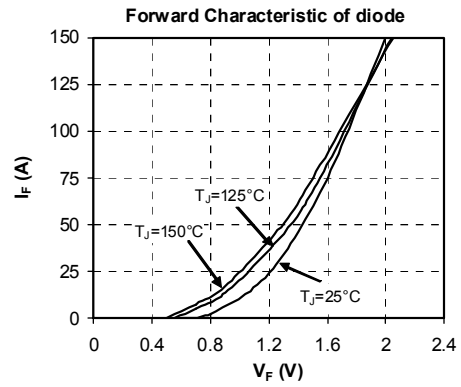
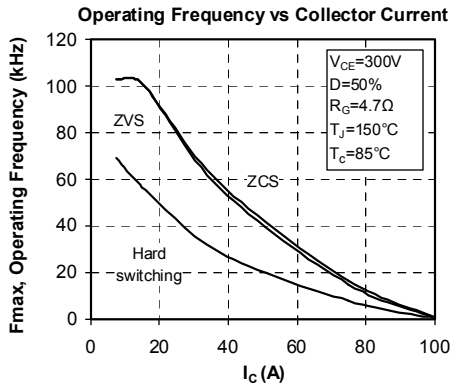
SP6-P Package outline (dimensions in mm)



See application note 1902 - Mounting Instructions for SP6-P (12mm) Power Modules on www.microsemi.com

Typical Performance Curve





Microsemi reserves the right to change, without notice, the specifications and information contained herein

Microsemi's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S. and Foreign patents pending. All Rights Reserved.